

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	("5990496").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/08/24 13:12
S2	37	nitride near3 semiconductor near3 laser and (ingan same (current near3 block\$3))	US-PGPUB; USPAT	OR	OFF	2004/08/24 13:15
S3	3	nitride near3 semiconductor near3 laser and (ingan near3 (current near3 block\$3)) and ridge	US-PGPUB; USPAT	OR	OFF	2004/08/24 14:33
S4	1	nitride near3 semiconductor near3 laser and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	US-PGPUB; USPAT	OR	OFF	2004/08/24 14:35
S5	1	nitride near3 semiconductor near3 laser and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/24 14:36
S6	10	nitride and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/24 14:36
S7	12	nitride and (current near3 block\$3 near3 (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1))) and ridge	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/24 14:41
S8	20	nitride and (current near3 block\$3 near3 (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/24 16:23
S9	1	("6031858").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/08/24 15:45
S10	11	cap near3 contact near3 layer\$1 and nitride near3 semiconductor near3 laser	US-PGPUB; USPAT	OR	OFF	2004/08/24 15:46
S11	14	nitride near3 based near3 laser and (current near3 block\$3 same (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/24 16:24
S12	109	nitride near3 semiconductor near3 laser and (current near3 (block\$3 or confin\$9)) and ridge	US-PGPUB; USPAT	OR	OFF	2004/08/23 15:07
S13	13	((nitride near3 base\$1) or (nitride-base\$1)) and ((buried near3 ridge) or (buried-ridge)) and (current near3 (block\$3 or confin\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 16:30

S14	3	((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))	US-PGPUB; USPAT	OR	OFF	2004/08/23 17:22
S15	4	((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:23
S16	1	((((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))) not (((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:22
S17	68	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:23
S18	5	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	US-PGPUB; USPAT	OR	OFF	2004/08/23 17:31
S19	0	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:29
S20	66	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth))	US-PGPUB; USPAT	OR	OFF	2004/08/23 17:30
S21	5	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:32
S22	9	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 (technique or process or procedure or method)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/08/23 17:33
S23	290	semiconductor near3 laser and nitride and ridge and current near3 block\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 10:05
S24	0	("2003/0067953").URPN.	USPAT	OR	OFF	2005/08/01 09:59
S25	1622	372/46.01.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 12:44
S26	568	S25 and ridge	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 10:05

S27	503	S26 not S23	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 10:17
S28	62	carrier near3 current near3 confinement	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 10:17
S29	41	S28 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 10:17
S30	0	372/46.01.ccls. and ridge and nitride and transverse near3 growth	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 12:44
S31	1	372/46.01.ccls. and ridge and nitride and transverse near3 growth	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 12:46
S32	9	372/46.01.ccls. and transverse near3 growth	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/01 12:47